

L Number	Hits	Search Text	DB	Time stamp
1	56795	flash adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:07
2	1534	(flash adj memory) and (ion adj implant\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 15:00
3	541	((flash adj memory) and (ion adj implant\$4)) and anneal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:17
4	430	((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:40
5	277	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:40
6	0	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj gate) same (active adj area))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 12:05
7	15	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (tunnel adj oxide) and (floating adj gate) and (control adj gate) and (active adj area)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 12:06
9	11	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (tunnel adj oxide) and (floating adj gate) and (control adj gate) and (active adj area)) and ((doped adj drain) or DDD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 12:07
10	92	(flash adj memory) and ((ion adj implant\$4) with anneal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:18
12	0	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (tunnel adj oxide) and (floating adj gate) and (control adj gate) and (active adj area)) and ((ion adj implant\$4) with anneal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:19
11	44	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and ((ion adj implant\$4) with anneal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:41
13	0	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (((ion adj implant\$4) with anneal\$4) same (ammonia or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:30

15	0	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (((ion adj implant\$4) with anneal\$4) same (ammonia or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:30
14	15	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (((ion adj implant\$4) with anneal\$4) and (ammonia or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:59
16	430	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:40
17	277	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:41
18	15	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (((ion adj implant\$4) with anneal\$4) and (ammonia or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:42
19	15	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode)) and (((ion adj implant\$4) with anneal\$4) and (ammonia or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:42
20	56795	flash adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:07
21	0	(flash adj memory) and ((ion adj implant\$4) same ((spike or repid) adj2 anneal\$4) same (ammonium or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:12
23	34	(flash adj memory) and (ion adj implant\$4) and (((spike or rapid) adj2 anneal\$4) same (ammonium or hydrogen or nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:19
25	34	(flash adj memory) and (ion adj implant\$4) and (((spike or rapid) adj2 anneal\$4) same (ammonium or hydrogen or nitrogen)) and implant\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:19
26	0	((flash adj memory) and (ion adj implant\$4) and (((spike or rapid) adj2 anneal\$4) same (ammonium or hydrogen or nitrogen)) and implant\$4) and (heat\$4 adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 14:59
27	0	(flash adj memory) and (ion adj implant\$4) and (((rapid or spike) adj3 anneal\$4) with (heat\$4 adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 15:04
28	0	(flash adj memory) and (ion adj implant\$4) and (((rapid or spike) adj3 anneal\$4) same (heat\$4 adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 15:04

29	1	(flash adj memory) and (ion adj implant\$4) and (anneal\$4 same (heat\$4 adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 15:04
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